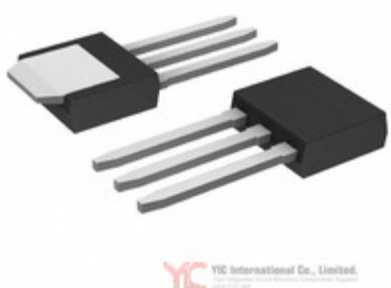

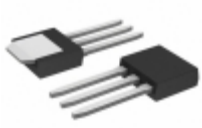
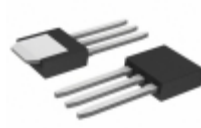






	<h2 style="color: #E67E22;">GP2M005A060PGH</h2>	
	Hersteller-Teilenummer:	GP2M005A060PGH
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 600V 4.2A IPAK
<p style="font-size: small;">Image may be representation. See specs for product details.</p>	Datenblätter:	 GP2M005A060PGH.pdf
	RoHs Status:	Bleifrei / RoHS-konform
	Lagerzustand:	New original, 7088 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS

Spezifikationen

Teilenummer	GP2M005A060PGH
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 600V 4.2A IPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	7088 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-251-3 Short Leads, IPak, TO-251AA
Supplier Device-Gehäuse	I-Pak
Verlustleistung (max)	98.4W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.2A (Tc)
Rds On (Max) @ Id, Vgs	2.1 Ohm @ 2.1A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	14nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	658pF @ 25V
Verpackung	Tube

GP2M005A060PGH ist neu im Original, Suche GP2M005A060PGH Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP2M005A060PGH Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP2M005A060PGH: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>GP2M005A050PG Global Power Technologies Group MOSFET N-CH 500V 4.5A IPAK</p>	 <p>GP2M005A060PG Global Power Technologies Group MOSFET N-CH 600V 4.2A IPAK</p>	 <p>GP2M008A060FGH Global Power Technologies Group MOSFET N-CH 600V 7.5A TO220F</p>	 <p>GP2M008A060CG Global Power Technologies Group MOSFET N-CH 600V 7.5A DPAK</p>
 <p>GP2M007A065HG Global Power Technologies Group MOSFET N-CH 650V 6.5A TO220</p>	 <p>GP2M005A060HG Global Power Technologies Group MOSFET N-CH 600V 4.2A TO220</p>	 <p>GP2M007A080F Global Power Technologies Group MOSFET N-CH 800V 7A TO220F</p>	 <p>GP2M005A060FG Global Power Technologies Group MOSFET N-CH 600V 4.2A TO220F</p>

heiße Teile

Mehr

⊗ GP200E1MTR-G1	↔ GP200EMTR-G1	⇒ GP200MTR-G1	D GP2A231LRSA	↔ GP2A25J0000F
⊣ GP2A25J0000F	⊗ GP2A25NJ	D GP2A28A1J00F	⇒ GP2A28N1J00F	↔ GP2AP002A00F
⊗ GP2AP002S00F	⊣ GP2AP003A10F	⊗ GP2AP007A00F	↔ GP2AP008T00F	↔ GP2AP030A00F
D GP2AP052A00F	⊗ GP2AP052A00F	⊣ GP2L26K2	⊗ GP2M002A060FG	↔ GP2M004A060PG
⇒ GP2M004A065FG	↔ GP2M004A065PG	⊗ GP2M005A050PG	⊣ GP2M005A060CG	↔ GP2M005A060FG
↔ GP2M008A060FGH	⇒ GP2M010A060F	D GP2M010A065F	⊗ GP2M011A090NG	⊣ GP2M012A080NG
⊗ GP2M020A050H	D GP2M020A060N	⇒ GP2S24J0000F	↔ GP2S27T3	↔ GP2S27T3J00F
⊣ GP2S27V6	⊗ GP2S29SVJ00F	↔ GP2S40JJ000F	⇒ GP2S700HCP	↔ GP2S700HCP
⊗ GP2W0004YP	⊣ GP2W0110YPS	⊗ GP2W0112YPOF	D GP2W0118YPS	↔ GP2W0150YP0F
↔ GP2W3104XP0F	⊗ GP2W3104YP0F	⊣ GP2W3106YP0F	⊗ GP2W3152YP0F	↔ GP2W3172XP0F

Contact us: Info@Y-IC.com

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